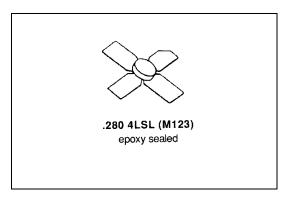


MS1642P

RF & MICROWAVE TRANSISTORS VHF, UHF GENERAL PURPOSE

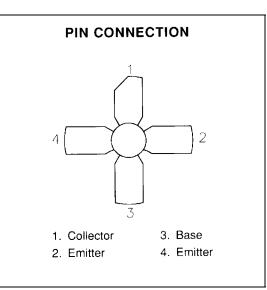
Features

- 400 MHz
- GOLD METALLIZATION
- P_{OUT} = 10 W MINIMUM
- G_P = 12 dB MINIMUM
- INFINITE VSWR CAPABILITY
- COMMON EMITTER CONFIGURATION



DESCRIPTION:

The MS1642 is a gold metallized silicon NPN transistor designed for general purpose amplifier applications in the VHF and UHF frequency bands. Diffused emitter ballast resistors and computer controlled wirebonding techniques ensure maximum device reliability and consistency.



ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
P _{DISS}	Power Dissipation*	27	W
I _{C(max)}	Device Current*	1.5	Α
T _{STG}	Storage Temperature	-65 to +150	οС
V _{CBO}	Collector – Base Voltage	60	V
V _{CEO}	Collector - Emitter Voltage	33	V
V _{EBO}	Emitter - Base Voltage	4.0	V

Thermal Data

R _{TH(J-C)}	Thermal Resistance Junction-case	6.4	°C/W			

^{*}Applies only to rated RF amplifier operation



MS1642P

ELECTRICAL SPECIFICATIONS (Tcase = 25°C) STATIC

Symbol	Test Conditions		Value			
	rest conditions		Min.	Тур.	Max.	Unit
Bvceo	I _C = 20 mA	I _E = 0 mA	33			V
Bvces	I _C = 20 mA	$I_C = 0 \text{ mA}$	60			V
Bvcbo	I _C = 20 mA	I _E = 0 mA	60			V
Bvebo	I _E = 2.0 mA	I _C = 0 mA	4.0			V
Icbo	V _{CB} = 30 V				1.0	mA
HFE	V _{CE} = 5 V	$I_C = 500 \text{ mA}$	20		100	

DYNAMIC

Symbol	Test Conditions			Value			
Syllibol		rest Conditions			Тур.	Max.	Unit
P _{IN}	f =400MHz	$P_{OUT} = 10W$	$V_{CC} = 28V$			0.65	W
G _P	f =400MHz	P _{out} = 10W	V _{CC} =28V	12			dB
ης	f =400MHz	P _{out} = 10W	V _{CC} =28V	50			%
Сов	f =1 MHz	V _{CB} =28V				12	pF

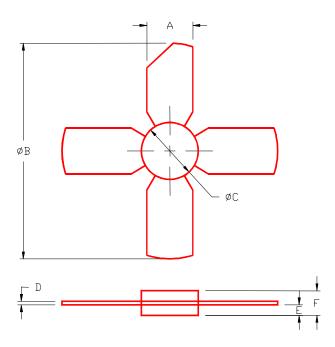
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PACKAGE MECHANICAL DATA

PACKAGE STYLE M123



	MINIMUM	MAXIMUM	MINIMUM	MAXIMUM
	INCHES/MM	INCHES/MM	INCHES/MM	INCHES/MM
Α	.220/5,59	,230/5,84		
В		1.055/26,8		
С	.275/6,99	.285/7,24		
D	.004/0,10	.006/0,15		
E	.050/1,27	.060/1,52		
F	.118/3,00	.130/3,30		